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Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/663,741
				Filing Date	September 17, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2811
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	M4065.0656/P656
Sheet	1	of	1		

## U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
Ch	A	6,673,648	01/06/2004	Lowrey	

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>

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## NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

*Ch*

02-15-05



Approved for use through 07/31/2008. OMB 0651-0031  
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
CA	A	US 2004/0035401	2/2004	Ramachandran et al.	
CA	B	US 2003/0212724	11/2003	Ovshinsky et al.	
CA	C	US 2003/0048744	3/2003	Ovshinsky et al.	
CA	D	US 2003/0212725	11/2003	Ovshinsky et al.	
CA	E	US RE 37,259E	7/2001	Ovshinsky	
CA	F	US 3,271,591	9/1966	Ovshinsky	
CA	G	US 3,961,314	6/1976	Klose et al.	
CA	H	US 3,966,317	6/1976	Wacks et al.	
CA	I	US 3,983,542	11/1976	Ovshinsky	
CA	J	US 3,988,720	10/1976	Ovshinsky	
CA	K	US 4,177,474	12/1979	Ovshinsky	
CA	L	US 4,267,261	5/1981	Hallman et al.	
CA	M	US 4,597,162	7/1986	Johnson et al.	
CA	N	US 4,608,296	8/1986	Keem et al.	
CA	O	US 4,637,895	1/1987	Ovshinsky et al.	
CA	P	US 4,646,266	2/1987	Ovshinsky et al.	
CA	Q	US 4,664,939	5/1987	Ovshinsky	
CA	R	US 4,668,968	5/1987	Ovshinsky et al.	
CA	S	US 4,670,763	6/1987	Ovshinsky et al.	
CA	T	US 4,673,957	6/1987	Ovshinsky et al.	
CA	U	US 4,678,679	7/1987	Ovshinsky	
CA	V	US 4,696,758	9/1987	Ovshinsky et al.	
CA	W	US 4,698,234	10/1987	Ovshinsky et al.	
CA	X	US 4,710,899	12/1987	Young et al.	
CA	Y	US 4,728,406	3/1988	Banerjee et al.	
CA	Z	US 4,737,379	4/1988	Hudgens et al.	
CA	A1	US 4,766,471	8/1988	Ovshinsky et al.	
CA	B1	US 4,769,338	9/1988	Ovshinsky et al.	
CA	C1	US 4,775,425	10/1988	Guha et al.	
CA	D1	US 4,788,594	11/1988	Ovshinsky et al.	
CA	E1	US 4,809,044	2/1989	Pryor et al.	
CA	F1	US 4,818,717	4/1989	Johnson et al.	
CA	G1	US 4,843,443	6/1989	Ovshinsky et al.	
CA	H1	US 4,845,533	7/1989	Pryor et al.	
CA	I1	US 4,853,785	8/1989	Ovshinsky et al.	
CA	J1	US 4,891,330	1/1990	Guha et al.	
CA	K1	US 5,128,099	7/1992	Strand et al.	
CA	L1	US 5,159,661	10/1992	Ovshinsky et al.	
CA	M1	US 5,166,758	11/1992	Ovshinsky et al.	
CA	N1	US 5,177,567	1/1993	Klersy et al.	
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CA	P1	US 5,335,219	8/1994	Ovshinsky et al.	
CA	Q1	US 5,359,205	10/1994	Ovshinsky	
CA	R1	US 5,341,328	8/1994	Ovshinsky et al.	
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				Art Unit	2811
				Examiner Name	Not Yet Assigned
Sheet	2	of	3	Attorney Docket Number	M4065.0656/P656

On	T1	US 5,414,271	5/1995	Ovshinsky et al.	
On	U1	US 5,534,711	7/1996	Ovshinsky et al.	
On	V1	US 5,534,712	7/1996	Ovshinsky et al.	
On	W1	US 5,536,947	7/1996	Klersy et al.	
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On	Y1	US 5,591,501	1/1997	Ovshinsky et al.	
On	Z1	US 5,596,522	1/1997	Ovshinsky et al.	
On	A2	US 5,687,112	11/1997	Ovshinsky	
On	B2	US 5,694,054	12/1997	Ovshinsky et al.	
On	C2	US 5,714,768	2/1998	Ovshinsky et al.	
On	D2	US 5,825,046	10/1998	Czubatyj et al.	
On	E2	US 5,912,839	6/1999	Ovshinsky et al.	
On	F2	US 5,933,365	8/1999	Klersy et al.	
On	G2	US 6,011,757	1/2000	Ovshinsky	
On	H2	US 6,087,674	7/2000	Ovshinsky et al.	
On	I2	US 6,141,241	10/2000	Ovshinsky et al.	
On	J2	US 6,339,544	1/2002	Chiang et al.	
On	K2	US 6,404,665	6/2002	Lowery et al.	
On	L2	US 6,429,064	8/2002	Wicker	
On	M2	US 6,437,383	8/2002	Xu	
On	N2	US 6,462,984	10/2002	Xu et al.	
On	O2	US 6,480,438	11/2002	Park	
On	P2	US 6,487,113	11/2002	Park et al.	
On	Q2	US 6,501,111	12/2002	Lowery	
On	R2	US 6,507,061	1/2003	Hudgens et al.	
On	S2	US 6,511,862	1/2003	Hudgens et al.	
On	T2	US 6,511,867	1/2003	Lowery et al.	
On	U2	US 6,512,241	1/2003	Lai	
On	V2	US 6,514,805	2/2003	Xu et al.	
On	W2	US 6,531,373	3/2003	Gill et al.	
On	X2	US 6,534,781	3/2003	Dennison	
On	Y2	US 6,545,287	4/2003	Chiang	
On	Z2	US 6,545,907	4/2003	Lowery et al.	
On	A3	US 6,555,860	4/2003	Lowery et al.	
On	B3	US 6,563,164	5/2003	Lowery et al.	
On	C3	US 6,566,700	5/2003	Xu	
On	D3	US 6,567,293	5/2003	Lowery et al.	
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On	F3	US 6,570,784	5/2003	Lowery	
On	G3	US 6,576,921	6/2003	Lowery	
On	H3	US 6,586,761	7/2003	Lowery	
On	I3	US 6,589,714	7/2003	Maimon et al.	
On	J3	US 6,590,807	7/2003	Lowery	
On	K3	US 6,593,176	7/2003	Dennison	
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On	N3	US 6,613,604	9/2003	Maimon et al.	
On	O3	US 6,621,095	9/2003	Chiang et al.	
On	P3	US 6,625,054	9/2003	Lowery et al.	
On	Q3	US 6,642,102	11/2003	Xu	

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<i>an</i>	R3	US 6,646,297	11/2003	Dennison	
<i>an</i>	S3	US 6,649,928	11/2003	Dennison	
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<i>an</i>	U3	US 6,671,710	12/2003	Ovshinsky et al.	
<i>an</i>	V3	US 6,673,700	1/2004	Dennison et al.	
<i>an</i>	W3	US 6,674,115	1/2004	Hudgens et al.	
<i>an</i>	X3	US 6,687,427	2/2004	Ramalingam et al.	
<i>an</i>	Y3	US 6,690,026	2/2004	Peterson	
<i>an</i>	Z3	US 6,696,355	2/2004	Dennison	
<i>an</i>	A4	US 6,687,153	2/2004	Lowery	
<i>an</i>	B4	US 6,707,712	3/2004	Lowery	
<i>an</i>	C4	US 6,714,954	3/2004	Ovshinsky et al.	

FOREIGN PATENT DOCUMENTS							
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		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)					

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PTO/SB/08a/b (08-03)  
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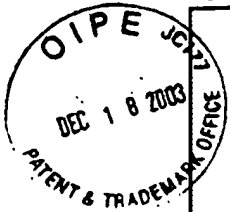
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CA	CA	YOJI KAWAMOTO et al., "Ionic Conduction in As <sub>2</sub> S <sub>3</sub> -Ag <sub>2</sub> S, GeS <sub>2</sub> -GeS <sub>2</sub> -GeS-Ag <sub>2</sub> S and P <sub>2</sub> S <sub>5</sub> -Ag <sub>2</sub> S Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404.	

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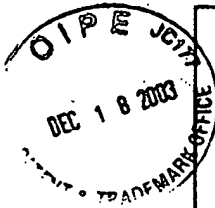
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Sheet	1	of	11
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CA	AA	2002/0000666	1/3/2002	Kozicki et al.	
CA	AB	2002/0072188	6/13/2002	Gilton	
CA	AC	2002/0106849	08/08/2002	Moore	
CA	AH	2002/0123169	09/05/2002	Moore et al.	
CA	AI	2002/0123170	09/05/2002	Moore et al.	
CA	AJ	2002/0123248	09/05/2002	Moore et al.	
CA	AK	2002/0127886	09/12/2002	Moore et al.	
CA	AL	2002/0132417	09/09/2002	Li	
CA	AF	2002/0160551	10/31/2002	Harshfield	
CA	AG	2002/0163828	11/07/2002	Krieger et al.	
CA	AM	2002/0168820	11/2002	Kozicki	
CA	AN	2002/0168852	11/14/2002	Harshfield et al.	
CA	AO	2002/0190289	12/19/2002	Harshfield et al.	
CA	AP	2002/0190350	12/19/2002	Kozicki et al.	
CA	AQ	2003/0001229	01/02/2003	Moore et al.	
CA	AR	2003/0027416	02/06/2003	Moore	
CA	AS	2003/0032254	02/13/2003	Gilton	
CA	AT	2003/0035314	02/20/2003	Kozicki	
CA	AU	2003/0035315	02/20/2003	Kozicki	
CA	AV	2003/0038301	02/27/2003	Moore	
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CA	AX	2003/0045049	03/06/2003	Campbell et al.	
CA	AY	2003/0045054	03/06/2003	Campbell et al.	
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CA	AA1	2003/0047772	03/13/2003	Li	
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CA	AC1	2003/0048519	03/13/2003	Kozicki	
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CA	AH1	2003/0096497	05/22/2003	Moore et al.	
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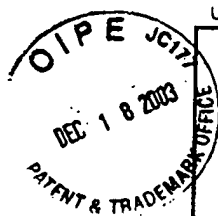
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Attorney Docket Number	M4065.0656/P656

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<input checked="" type="checkbox"/>	AS2	5,789,277	8/1998	Zahorik et al.	
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<input checked="" type="checkbox"/>	AU2	5,818,749	10/06/1998	Harshfield	
<input checked="" type="checkbox"/>	AV2	5,841,150	11/1998	Gonzalez et al.	
<input checked="" type="checkbox"/>	AW2	5,846,889	12/1998	Harbison et al.	
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<input checked="" type="checkbox"/>	AD3	6,031,287	2/29/2000	Harshfield	
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<input checked="" type="checkbox"/>	AP3	6,348,365	2/19/2002	Moore et al.	
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		Filing Date	September 17, 2003
		First Named Inventor	Terry L. Gilton
		Art Unit	N/A
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	M4065.0656/P656
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<input checked="" type="checkbox"/>	AR3	6,376,284	4/2002	Gonzalez et al.	
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<input checked="" type="checkbox"/>	AZ3	6,469,364	10/2002	Kozicki	
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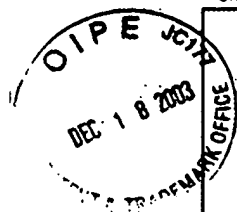
FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (If known)					
<i>g</i>	BA	56126916		10/19981	Akira et al.		
<i>h</i>	BB	WO 97/48032		12/18/1997	Kozicki et al.		
<i>h</i>	BC	WO 99/28914		06/10/1999	Kozicki et al.		
<i>g</i>	BD	WO 00/48196		08/17/2000	Kozicki et al.		
<i>h</i>	BE	WO 02/21542		03/14/2002	Kozicki et al.		

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		First Named Inventor	Terry L. Gilton
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		Attorney Docket Number	M4065.0656/P656
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
an	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
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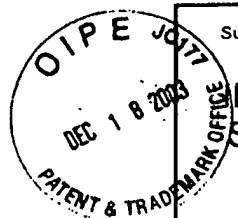
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## Complete if Known

Application Number	10/663,741
Filing Date	September 17, 2003
First Named Inventor	Terry L. Gilton
Group Art Unit	N/A
Examiner Name	Not Yet Assigned

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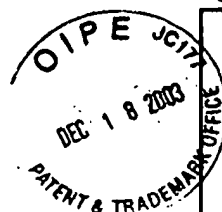
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Group Art Unit	N/A
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0656/P656

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		Group Art Unit	N/A		
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Sheet	7	of	11	Attorney Docket Number	M4065.0656/P656

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